There has been considerable interest in the 3d transition metal disulfides having pyrite structure to study metal-insulator transition in connection with the Mott-Hubbard model. (1) Recently, by high pressure electrical measurement Wilson and Pitt²) have found that a metal-insulator transition in NiS₂ occurs in the vicinity of 32 kbar at room temperature. They also have pointed out that for the semiconducting NiS₂ there is a lattice parameter greater by 0.03Å than would have occured in a metallic phase.

In the present study, we carried out X-ray diffraction measurement on NiS₂ at room temperature up to 100 kbar in order to clarify if the transition is associated with a change in crystal structure and/or volume.

meter a=5.687Å were prepared by chemical vapour transport with chlorine. A powdered sample of the single crystals was filled in a 0.3 mm hole in the center of a boron-epoxy disk, which was pressed between Bridgman anvils. 3)

A pressure clamp vessel including the anvils was mounted on a goniometer of a Guinier focusing camera. Diffraction pattern by Mo-Ka radiation was recorded on a curved film with a radius of 114.6 mm that allows a dispersion equal to maximum 20 angle of 45°. The pressure on the sample was calibrated by intimately mixing NiS2 with CsCl as an internal standard for pressure because almost every line of NaCl overlaps the lines of NiS2. The pressure-volume relation for CsCl calculated by Decker⁴⁾ was used